Serial No. 10/689,936 IIZ.003D2C

Amendment Under 37 C.F.R. 1.312 dated July 1, 2005

Amendments to the Claims

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

Claims 1-26 (Canceled)

Claim 27 (Currently Amended): A method for fabricating a semiconductor apparatus comprising:

forming a semiconductor integrated circuit on a first surface of a semiconductor substrate:

forming a base member of insulating material on the first surface of the semiconductor substrate;

forming a conductive layer directly on the first surface of the semiconductor substrate, the conductive layer being connected to the semiconductor integrated circuit and having an extended portion that extends onto a top surface of the base member;

placing the first surface of the semiconductor substrate having the semiconductor integrated circuit, the base member and the conductive layer thereon as facing a connection substrate;

connecting the extended portion of the conductive layer to the connection substrate; and

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supplying a sealing member in a space between the [[two]] semiconductor substrate and the connection substrate, after said connecting,

the base member and the sealing member having a same thermal expansion coefficient,

the conductive layer is formed so that the extended portion extends onto an entirety of the top surface of the base member.

Claim 28 (Previously Presented): A method according to claim 27, wherein the base member and the sealing member are a polymide resin.

Claims 29-31 (Canceled)